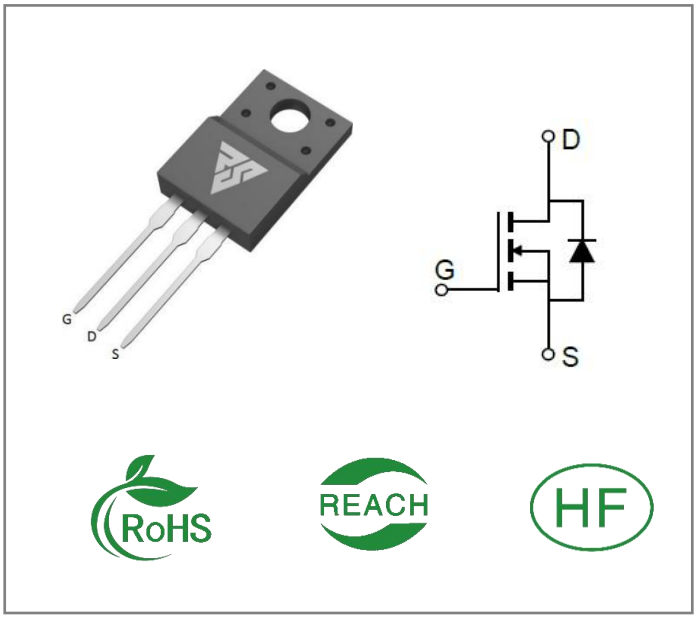
V_{DS}	$R_{DS(on)typ}$	I_D@25℃
800V	125mΩ	28A



Applications:

- Switch Mode Power Supplies
- High Voltage DC/DC Converters
- Battery Chargers
- Motor Drives
- Pulsed Power Applications

Features:

- Wide Bandgap SiC MOSFET Technology
- Low On-Resistance with High Blocking Voltage
- Low Capacitances with High-Speed Switching
- Low Reverse Recovery (Q_{rr})
- Easy to Parallel and Simple to Drive
- Robust against Parasitic Turn on Even 0V Turn off Gate Voltage

Benefits:

- Reduced Switching Losses
- Increased System Switching Frequency
- Increased Power Density
- Reduction of Heat Sink Requirements
- Reduced EMI

Ordering Information

Part Number	Package	Marking	Packing	Qty.
RSM080130F	TO-220F	RSM080130F	Tube	50 PCS

Maximum Ratings (TJ= 25℃ unless otherwise specified)

Symbol	Parameter	Value	Unit	Test Conditions	Note
V_{DS}	Drain - Source Voltage	800	V	V_{GS}=0V,I_D =100μA	
V_{GS}	Gate - Source Voltage	-10/+22	V	Absolute maximum values	
V_{GSop}	Gate - Source Voltage	0/+18	V	Recommended operational values	
I_D	Continuous Drain Current	28 22	A	V_{GS}=15V,T_C =25℃ V_{GS}=15V,T_C =100℃	
I_{DM}	Pulsed Drain Current	56	A		
P_D	Power Dissipation	36	W	T_C =25℃, T_J =175℃	
T_J, T_{stg}	Operating Junction and StorageTemperature	-55 to + 175	℃		

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Electrical Characteristics (TJ= 25℃ unless otherwise specified)

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions	Note
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	800			V	V_{GS}=0V,I_D =250μA	
$V_{GS(th)}$	Gate Threshold Voltage	2.7	3.6	4.5	V	V_{GS}= V_{DS}, I_D=5.2mA	
I_{DSS}	Zero Gate Voltage Drain Current		1	50	μA	V_{DS}= 800V, V_{GS}=0V TJ =25℃	
I_{GSS}	Gate-Source Leakage Current			250	nA	V_{GS}=18V, V_{DS}= 0V	
$R_{DS(on)}$	Drain-Source on-state Resistance		125	180	mΩ	V_{GS}=15V, I_D =12A	
			95	120		V_{GS}=18V, I_D =12A	
C_{iss}	Input Capacitance		770		pF	V_{GS}=0V, V_{DS}=50V f=1MHz，T_J=25℃	
C_{oss}	Output Capacitance		162				
C_{rss}	Reverse Transfer Capacitance		11.2				
$t_{d(on)}$	Turn-On Delay Time		16		ns	V_{DD} =500V V_{GS} =0/15 V I_D = 12A $R_{G(ext)}$ = 2Ω	
t_r	Rise Time		48				
$t_{d(off)}$	Turn-Off Delay Time		21				
t_f	Fall Time		34				
$R_{G(int)}$	Internal Gate Resistance		0.87		Ω	f=1MHz, V_{AC}=25mV	
Q_{gs}	Gate to Source Charge		13		nC	V_{DS}=500V V_{GS}=0/15V I_D=12A T_J=25℃	
Q_{gd}	Gate to Drain Charge		13				
Q_g	Total Gate Charge		33				

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Reverse Diode Characteristics (TJ= 25℃ unless otherwise specified)

Symbol	Parameter	Typ.	Max	Unit	Test Conditions	Note
V_{SD}	Diode Forward Voltage	3.2		V	V_{GS}=0V, I_S =6A T_J = 25℃	
I_S	Continuous Diode Forward Current	6		A	V_{GS}=0V,T_J= 25℃	
t_{rr}	Reverse Recovery time	14		ns	V_{GS}=0V I_{SD}=12A V_R=500V di/dt=1200 A/μs T_J= 25℃	
Q_{rr}	Reverse Recovery Charge	56		nC		
I_{rrm}	Peak Reverse Recovery Current	6.5		A		

Thermal Characteristics (TJ= 25℃ unless otherwise specified)

Symbol	Parameter	Typ.	Unit	Test Conditions	Note
$R_{\theta JC}$	Thermal Resistance from Junction to Case	3.7	℃/W		

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Typical Feature Curve

Figure 1. Output Characteristics Tj=25℃

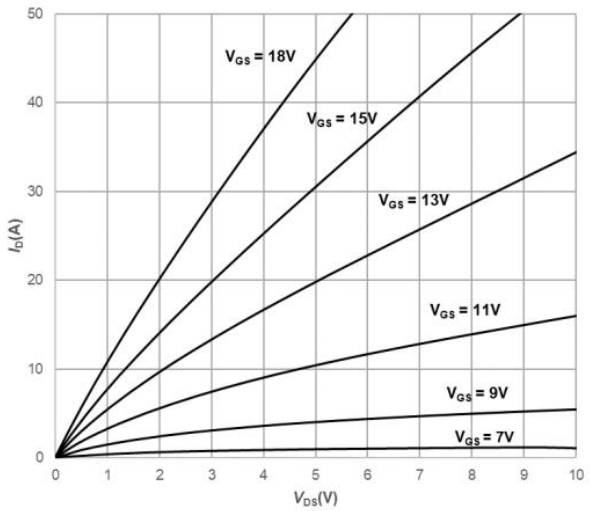


Figure 2. Output Characteristics Tj=175℃

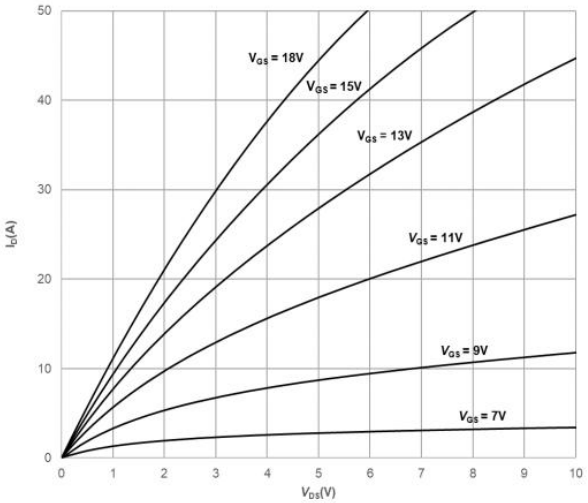


Figure 3. Typical Transfer Characteristics

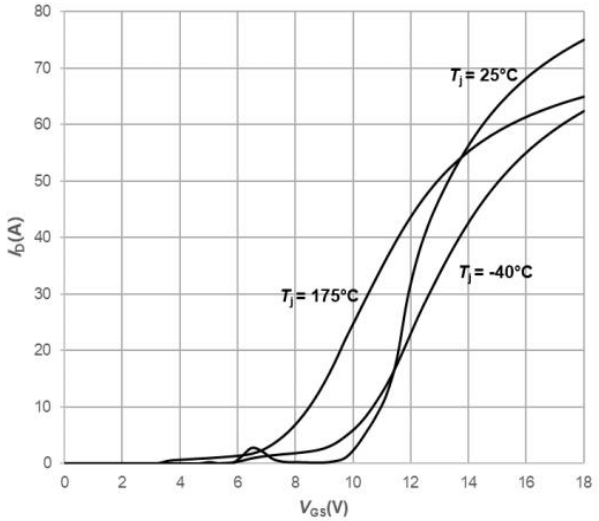


Figure 4. Normalized On-Resistance vs. Temperature

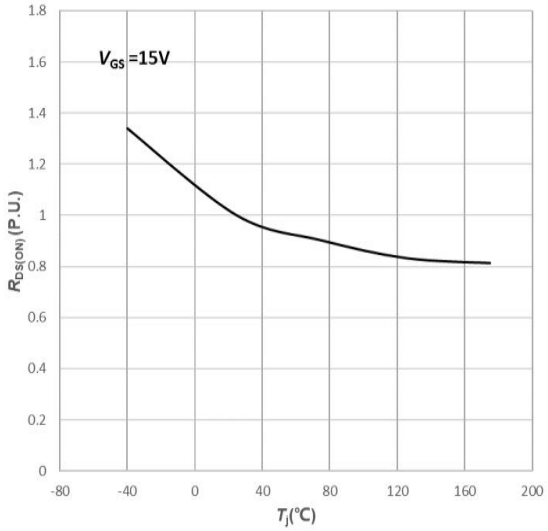


Figure 5. Normalized On-Resistance vs. Drain Current For

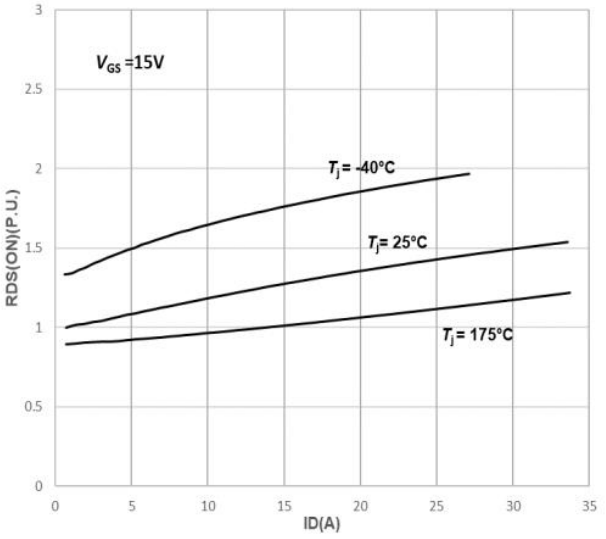
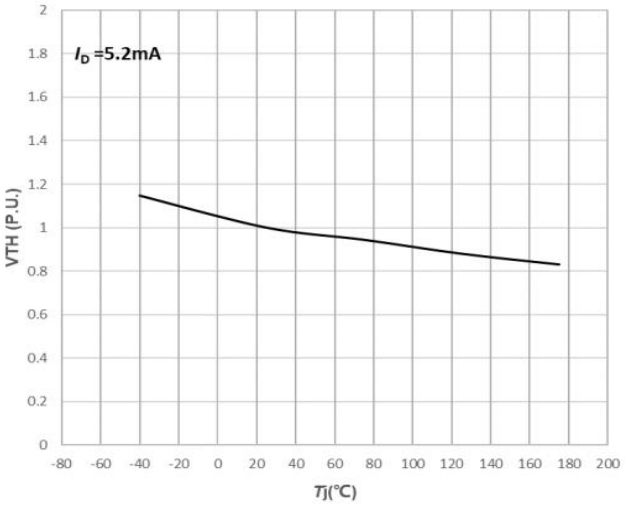


Figure 6. Normalized Threshold Voltage vs. Temperature Current For Various Temperatures



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Figure 7. Capacitances vs. Drain-Source Voltage (0-200V)

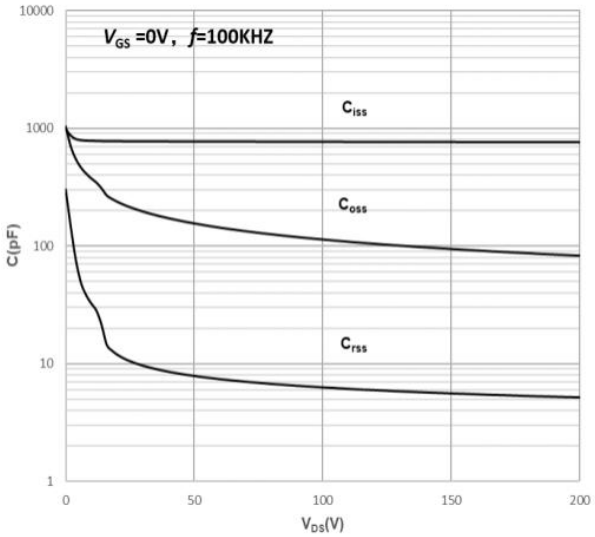


Figure 8. Capacitances vs. Drain-Source Voltage (0-600V)

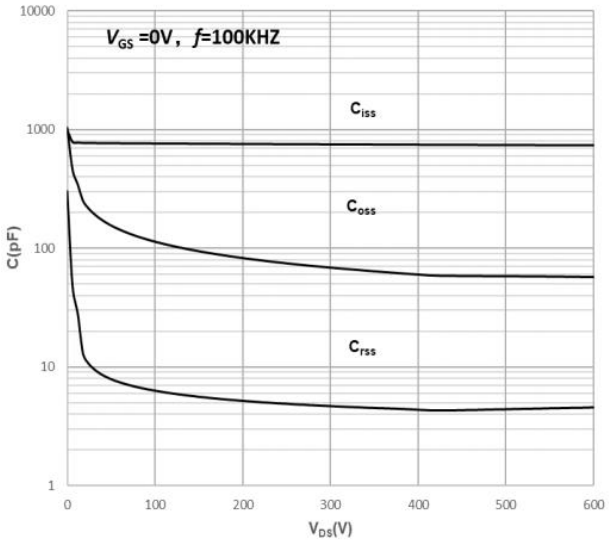
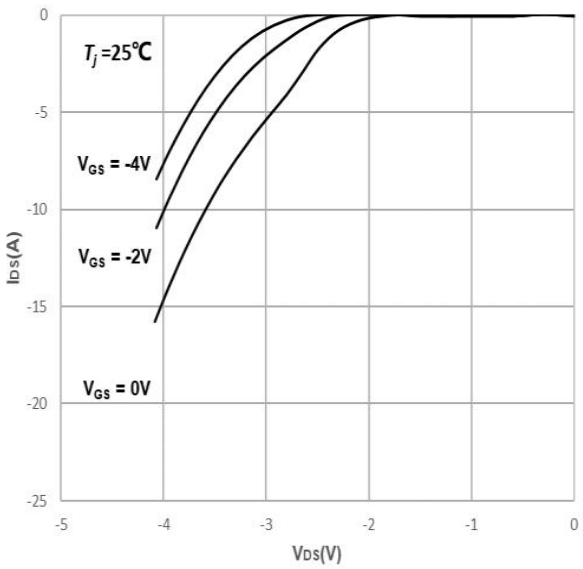
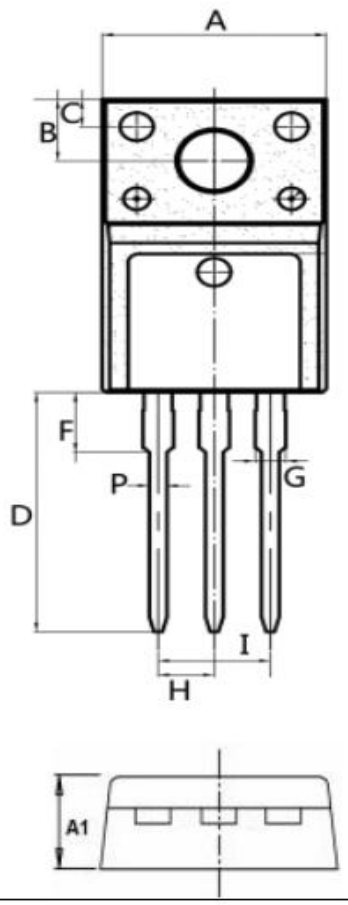


Fig9. Body Diode Characteristics



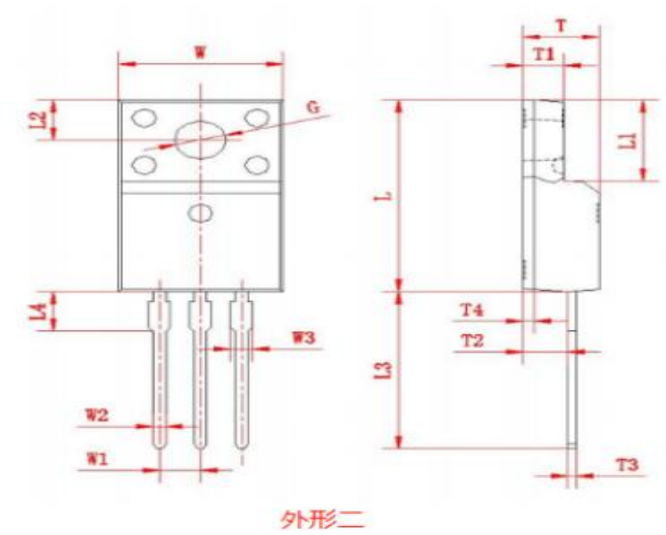
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Package outline drawing(TO-220F Unit: mm)



外形一

Dim.	Min.	Max.
A	9.95	10.36
A1	4.5	5.0
B	2.95	3.25
C	1.25	1.45
D	12.60	13.60
E	0.40	0.60
F	2.8	3.5
G	1.30	1.45
H	(2.54)	
I	(5.08)	
J	4.60	4.75
K	2.45	2.65
L	6.5	6.8
M	15.4	16.0
N	2.25	3.05
O	0.45	0.55
P	0.70	0.90
All Dimensions in millimeter		



外形二

Dim.	Min.	Max.
W	9.95	10.36
W1	(2.54)	
W2	0.70	0.90
W3	1.25	1.47
L	15.67	16.07
L1	6.48	6.88
L2	3.2	3.4
L3	12.6	13.6
L4	(3.23)	
T	4.50	4.90
T1	2.34	2.74
T2	2.25	2.95
T3	0.45	0.60
T4	(0.70)	
G	3.08	3.28
All Dimensions in millimeter		

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